Unit: mm

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSVI)

# **TPC8124**

### Lithium Ion Battery Applications **Power Management Switch Applications**

- Small footprint due to small and thin package
- Low drain-source ON-resistance: RDS (ON) = 6.1 m $\Omega$  (typ.)
- Low leakage current:  $I_{DSS} = -10 \mu A \text{ (max) (V}_{DS} = -40 \text{ V)}$
- Enhancement mode:  $V_{th}$  = -0.8 to -2.0 V ( $V_{DS}$  = -10 V,  $I_D$  = -0.5mA)

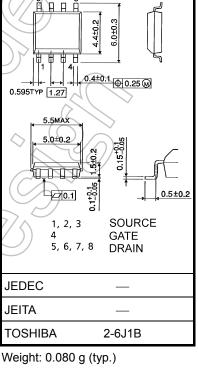
#### **Absolute Maximum Ratings (Ta = 25°C)**

Characteri	stics	Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-40	V
Drain-gate voltage (Ro	<sub>SS</sub> = 20 kΩ)	$V_{DGR}$	-40	∨
Gate-source voltage		$V_{GSS}$	-25/+20	V
Drain current	DC (Note 1)	ID	-12	^
	Pulse (Note 1)	I <sub>DP</sub>	-48	
Drain power dissipatio	n (t = 10 s) (Note 2a)	PD	1.9	W
Drain power dissipation	n (t = 10 s) (Note 2b)	Pp	1.0	w
Single pulse avalanche	e energy (Note 3)	EAS	134	mJ
Avalanche current	(Note 1)	// JIAR	-12	A
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature ra	ange	□ T <sub>stg</sub>	-55 to 150	°C

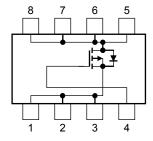
Note 1, Note 2, Note 3: See the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating

temperature/current/voltage, etc.) are within the absolute maximum



#### **Circuit Configuration**



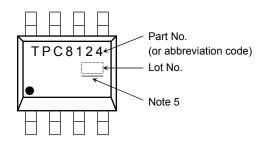
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

#### **Thermal Characteristics**

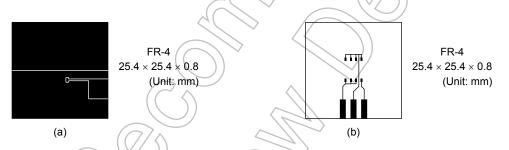
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	125	°C/W

#### Marking (Note 4)



Note 1: Ensure that the channel temperature does not exceed 150°C.

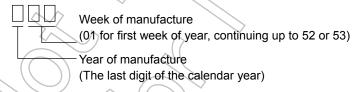
Note 2: (a)Device mounted on a glass-epoxy board (a) (b)Device mounted on a glass-epoxy board (b)



Note 3:  $V_{DD} = -24 \text{ V}$ ,  $T_{ch} = 25 \,^{\circ}\text{C}$  (initial), L = 1.0 mH,  $R_G \neq 25 \,\Omega$ ,  $I_{AR} = -12 \,\text{A}$ 

Note 4: • on lower left of the marking indicates Pin 1.

\* Weekly code: (Three digits)



Note 5: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

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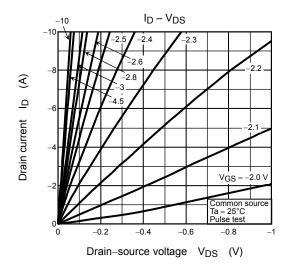
## **Electrical Characteristics (Ta = 25°C)**

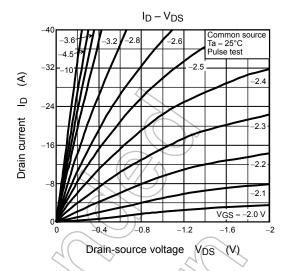
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curre	nt	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cut-OFF curr	ent	I <sub>DSS</sub>	$V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-10	μΑ
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-40	_	_	V
		V <sub>(BR)DSX</sub>	$I_D = -10 \text{ mA}, V_{GS} = 10 \text{ V}$ (Note 6)	-30	_	_	V
Gate threshold volt	age	V <sub>th</sub>	$V_{DS} = -10 \text{ V}, I_D = -0.5 \text{ mA}$	-0.8	) /_	-2.0	V
Drain-source ON-resistance		Pro (OV)	$V_{GS} = -4.5 \text{ V}, I_D = -6 \text{ A}$	) <u> </u>	7.7	10	- mΩ
		R <sub>DS</sub> (ON)	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -6 A	$\mathcal{P}$	6.1	8	
Input capacitance		C <sub>iss</sub>			4750	_	
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	540	_	pF
Output capacitance		Coss		_	620	_	
	Rise time	t <sub>r</sub>	V <sub>GS</sub> 0 V   I <sub>D</sub> = -6 A   C   C   C   C   C   C   C   C   C	- (	29	<u> </u>	- ns
Cuitabing time	Turn-ON time	t <sub>on</sub>			11/	) —	
Switching time	Fall time	t <sub>f</sub>	A.W. W. B. E. E. B. S.	7	110	_	
	Turn-OFF time	t <sub>off</sub>	$V_{DD} \approx -20 \text{ V}$ Duty $\leq$ 1%, $t_W = 10 \mu\text{s}$		390		
Total gate charge (gate-source plus gate-drain)		Qg	V <sub>DD</sub> ≈ -32 V, V <sub>G</sub> \$ = -10 V,	/_	104	_	
Gate-source charge 1		Q <sub>gs1</sub>	I <sub>D</sub> = -12 A	_	10	_	nC
Gate-drain ("miller") charge		Q <sub>gd</sub>			27		

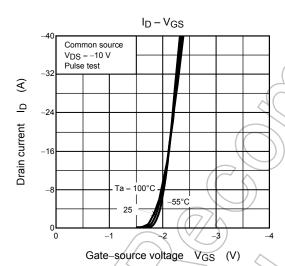
# Source-Drain Ratings and Characteristics (Ta = 25°C)

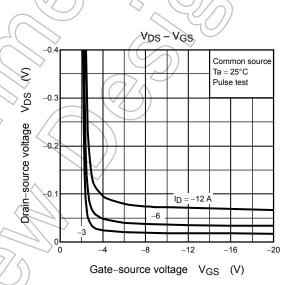
Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	IDRR		_	_	-48	Α
Forward voltage (diod	de)	V <sub>DSF</sub>	$I_{DR} = -12 \text{ A}, V_{GS} = 0 \text{ V}$			1.2	V

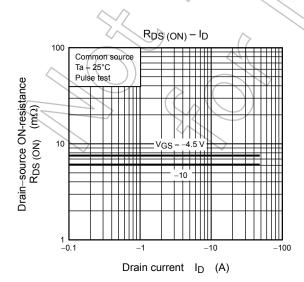
Note 6: VDSX mode (the application of a plus voltage between gate and source) may cause decrease in maximum rating of drain-source voltage.



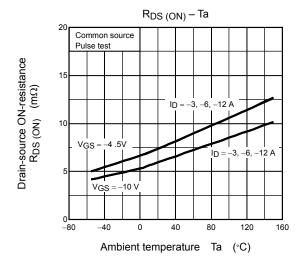


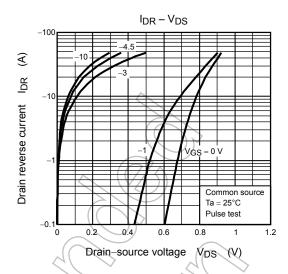


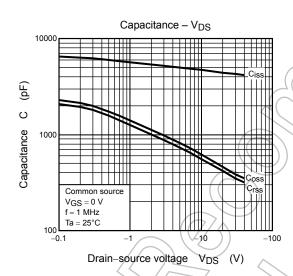


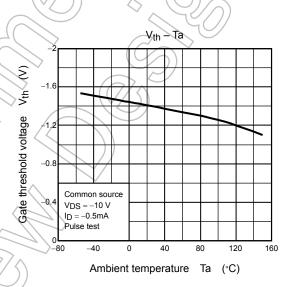


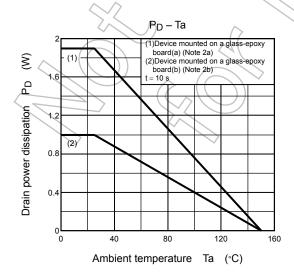
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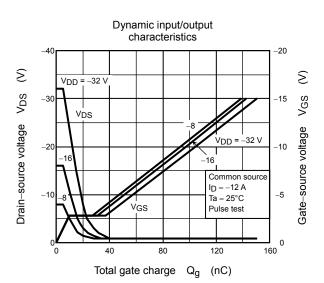




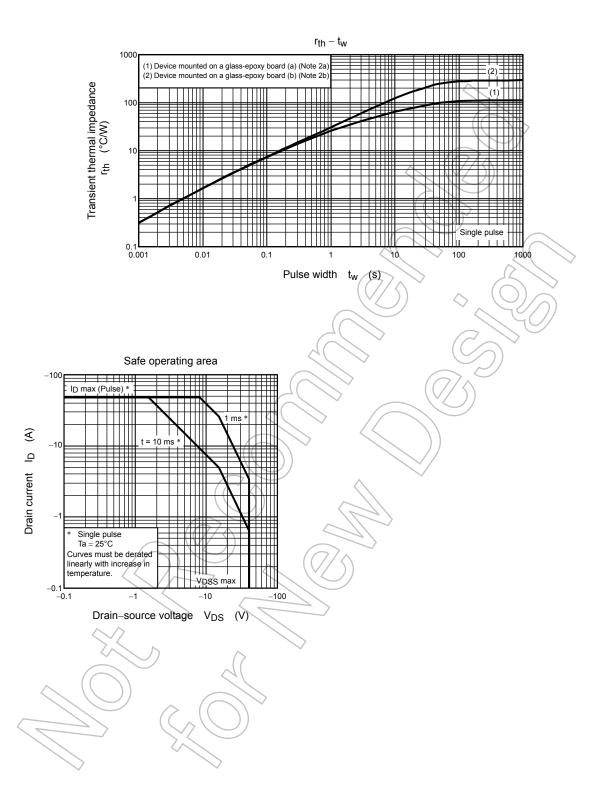








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